

SLG7MD47701

Full/Half Bridge PWM Motor Driver

The SLG7MD47701 is a versatile solution for Full and Half-Bridge motor driving applications. Configurable outputs via control of input (AIN1 and AIN2), PWM, and nSLEEP pin allow for fine motor control. An efficient integrated solution for a variety of low-voltage and battery-powered motor control applications, optimized for use in small devices where size and power efficiency are critical factors.

Driver FETs and FET control circuitry are integrated and reduce system component count while prioritizing power efficiency. The SLG7MD47701 operates with minimal energy expenditure due to its low power consumption. Its compact design, versatile functionality, low power consumption, and sleep mode configuration are possible due to the availability of nSLEEP pin.

Additionally, the device includes important protection features such as undervoltage lockout, overcurrent protection, and thermal shutdown, ensuring reliable and safe operation in various environments.

This is a pre-configured device. The configuration of this device can be modified to meet specific requirements at no additional NRE costs. Other functions and features may also be added. For more information on custom configurations visit the [GreenPAK website](#).

Click [here](#) to download the GreenPAK file for the SLG7MD47701 design.

Email GreenPAKSupport@renesas.com for more information and GreenPAK design support.

Features

- Four high voltage high current drive GPOs
- Current up to 1.5 A RMS per GPO/H-Bridge
- Low power consumption
- Pb-Free/RoHS compliant
- Halogen-free
- STQFN-20 package

Applications

- Cameras
- Toys
- Robotics
- Medical devices
- DSLR lenses
- Motor control

Output Summary

- High Voltage High Current Drive GPO

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1. Block Diagram

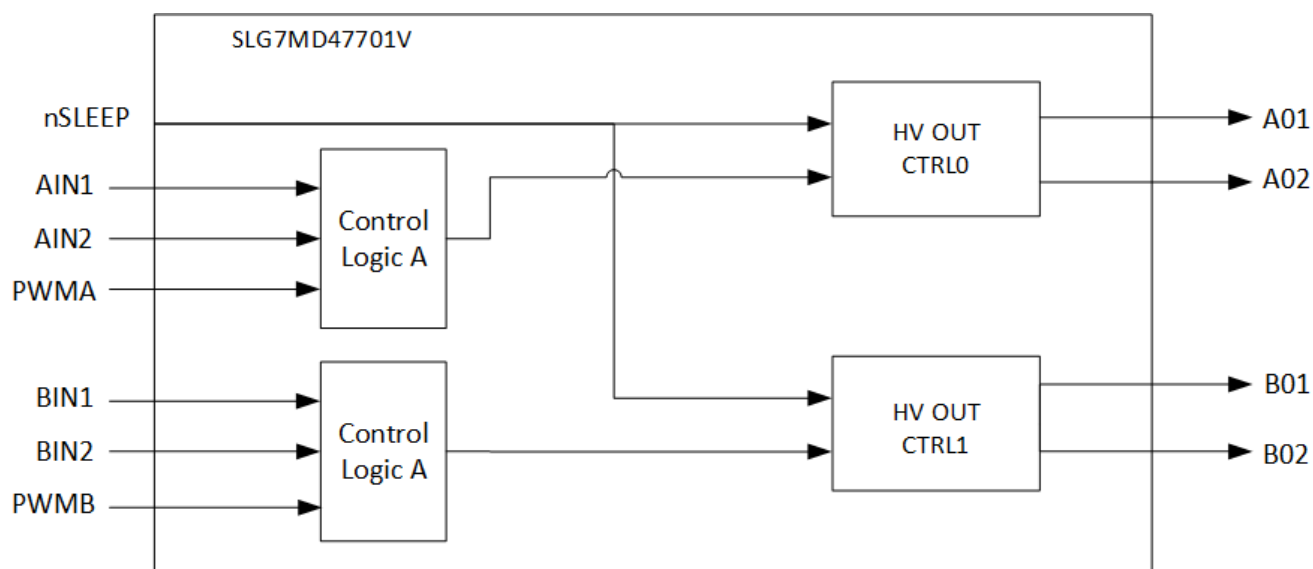


Figure 1. Functional Diagram

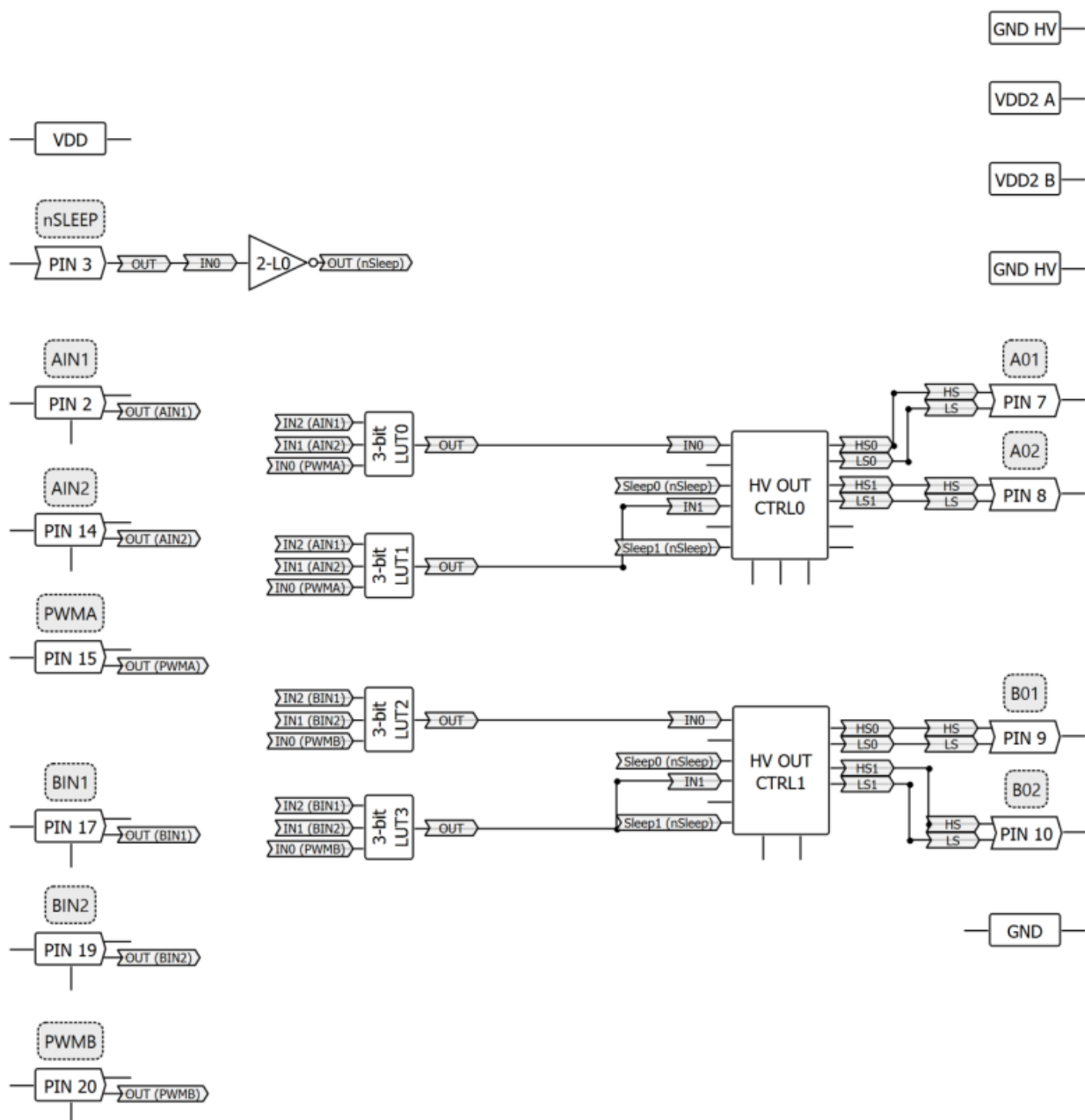
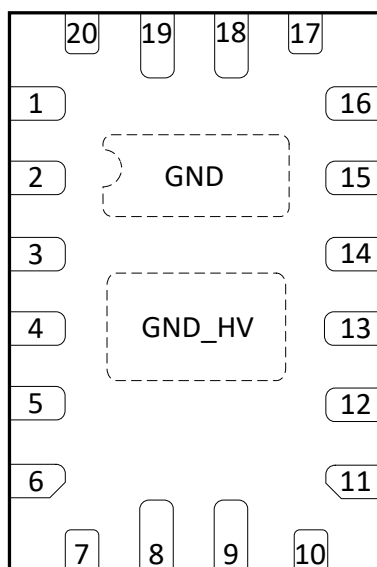


Figure 2. Block Diagram

2. Pin Information

2.1 Pin Assignments



STQFN-20L
(Top View)

Figure 3. Pin Assignments - Top View

2.2 Pin Descriptions

Pin #	Pin Name	Type	Description	Internal Resistor
1	V _{DD}	PWR	Supply Voltage	--
2	AIN1	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down
3	nSLEEP	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down
4	GND_HV	GND	Ground	--
5	SENSE_A	Analog Input/Output	Analog Input/Output	Floating
6	V _{DD2_A}	PWR	Supply Voltage	--
7	A01	High Drive Output	High Drive Push-Pull	Floating
8	A02	High Drive Output	High Drive Push-Pull	Floating
9	B01	High Drive Output	High Drive Push-Pull	Floating
10	B02	High Drive Output	High Drive Push-Pull	Floating
11	V _{DD2_B}	PWR	Supply Voltage	--
12	SENSE_B	Analog Input/Output	Analog Input/Output	Floating
13	GND_HV	GND	Ground	--
14	AIN2	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down

Pin #	Pin Name	Type	Description	Internal Resistor
15	PWMA	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down
16	NC	--	Keep Floating or Connect to GND	--
17	BIN1	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down
18	GND	GND	Ground	--
19	BIN2	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down
20	PWMB	Digital Input	Digital Input without Schmitt Trigger	1 MΩ Pull-Down

3. Specifications

3.1 Absolute Maximum Ratings

Parameter		Description	Min	Max	Unit
Supply Voltage on V _{DD} relative to GND			-0.3	7.0	V
Supply Voltage on V _{DD2} relative to GND			-0.3	18	V
DC Input Voltage			GND - 0.5	V _{DD} + 0.5	V
Maximum V _{DD} Average or DC Current		(Through V _{DD} or GND Pin) for V _{DD} Group	--	120	mA
Maximum V _{DD2} Average or DC Current		Through each V _{DD2_A} , V _{DD2_B} , SENSE_A, or SENSE_B Pin	--	2000	mA
Maximum Average or DC Current (V _{DD2} Power Supply)	Push-Pull/ Half Bridge	Through V _{DD2} High Current Group Pins	--	1500	mA
Maximum Pulsed Current Sink/Sourced per HV HD Pin		Pulse Width < 0.5 ms; Duty Cycle < 2 %	--	Internally limited by OCP	mA
Current at Input Pin		Through V _{DD} Group Pin	-0.1	1.0	mA
Input Leakage Current (Absolute Value)			--	1000	nA
Storage Temperature Range			-65	150	°C
Junction Temperature			--	150	°C
ESD Protection (Human Body Model)			4000	--	V
ESD Protection (Charged Device Model)			1300	--	V
Moisture Sensitivity Level			1		

3.2 Thermal Information

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	Θ_{JA}	4L JEDEC PCB	--	--	65	°C/W
		4L JEDEC PCB with a thermal vias that connect thermal pad through all layers of the PCB	--	--	46	°C/W
Junction-to-case (top) Thermal Resistance	$\Theta_{JC(top)}$		--	23.50	--	°C/W
Junction-to-board Thermal Resistance	Θ_{JB}		--	25.51	--	°C/W

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Junction-to-case (top) Characterization Parameter	$\Psi_{JC(top)}$		--	6.80	--	°C/W
Junction-to-board Characterization Parameter	Ψ_{JB}		--	24.44	--	°C/W

3.3 Electrical Specifications

Parameter	Symbol	Condition/Note	Min	Typ	Max	Unit
Supply Voltage	V_{DD}		2.3	3.3	5.5	V
Supply Voltage	V_{DD_A}		3	12	13.2	V
Supply Voltage	V_{DD_B}		3	12	13.2	V
Operating Temperature	T_A		-40	25	85	°C
Capacitor Value at V_{DD}	C_{VDD}		0.1	--	--	μF
Input Capacitance	C_{IN}		--	4	--	pF
Quiescent Current V_{DD} Side	I_{Q_VDD}	Static inputs and floating outputs	--	1	--	μA
Quiescent Current V_{DD2_A} Side	$I_{Q_VDD2_A}$	Static inputs and floating outputs	--	--	--	μA
Quiescent Current V_{DD2_B} Side	$I_{Q_VDD2_B}$	Static inputs and floating outputs	--	--	--	μA
HIGH-Level Input Voltage ^[3]	V_{IH}	Logic Input ^[1]	$0.7 \times V_{DD}$	--	$V_{DD} + 0.3$	V
LOW-Level Input Voltage ^[3]	V_{IL}	Logic Input ^[1]	GND - 0.3	--	$0.3 \times V_{DD}$	V
HIGH-Level Output Voltage for V_{DD2} High Current Group	V_{OH2}	Push-Pull, $V_{DD} = 5 \pm 10\%$, $I_{OH2} = 10$ mA	4.496	--	--	V
		Push-Pull, $V_{DD} = 9$ V $\pm 10\%$, $I_{OH2} = 10$ mA	8.097	--	--	V
		Push-Pull, $V_{DD} = 12$ V $\pm 10\%$, $I_{OH2} = 10$ mA	10.797	--	--	V
LOW-Level Output Voltage for V_{DD2} High Current Group	V_{OL2}	Push-Pull, $V_{DD} = 5 \pm 10\%$, $I_{OL2} = 10$ mA	--	--	0.004	V
		Push-Pull, $V_{DD} = 9$ V $\pm 10\%$, $I_{OL2} = 10$ mA	--	--	0.004	V
		Push-Pull, $V_{DD} = 12$ V $\pm 10\%$, $I_{OL2} = 10$ mA	--	--	0.004	V
Pull-Down Resistance $T_J = -40$ °C to 85 °C	R_{PULL_DOWN}	Pull-down on PINs 2, 3, 14, 15, 17, 19, 20	--	1000	--	kΩ
Pull-Down Resistance $T_J = -40$ °C to 150 °C		Pull-down on PINs 2, 3, 14, 15, 17, 19, 20	--	1000	--	kΩ
Startup Time	T_{SU}	From V_{DD} rising past PON_{THR}	--	1	2	ms

Parameter	Symbol	Condition/Note	Min	Typ	Max	Unit
Power-On Threshold	PON _{THR}	V _{DD} level required to start up the chip	1.8	1.98	2.16	V
Power-Off Threshold	POFF _{THR}	V _{DD} level required to switch off the chip	1.33	1.55	1.83	V
[1] No hysteresis. [2] DC or average current through any pin should not exceed value given in Absolute Maximum Conditions. [3] ESD resistor should be taken into consideration when using pull-up/pull-down resistors. It may affect V_{IH} and V_{IL}. [4] Guaranteed by Design.						

3.4 HV Output Electrical Specifications (Full Bridge or Half Bridge Modes)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Rise Time HV OUT	t _R	V _{DD2} = 5 V, 16 Ω to GND, 10 % to 90 % V _{DD2} , T _J = -40 °C to 150 °C	81	116	156	ns
Fall Time HV OUT	t _F	V _{DD2} = 5 V, 16 Ω to GND, 90 % to 10 % V _{DD2} , T _J = -40 °C to 85 °C	80	115	198	ns
		V _{DD2} = 5 V, 16 Ω to GND, 90 % to 10 % V _{DD2} , T _J = -40 °C to 150 °C	80	115	225	ns
Dead Band Time of HV_GPOx_HD in Pre-driver Mode (not for Driver Mode) (Break before Making for Full Bridge and Half Bridge Modes)	T _{DEAD}	V _{DD2} = 3 V, T _J = -40 °C to 150 °C	--	337	--	ns
		V _{DD2} = 5 V, T _J = -40 °C to 150 °C	--	75	--	ns
		V _{DD2} = 13.2 V, T _J = -40 °C to 150 °C	--	91	--	ns
HS FET on Resistance (SENSE, GND_HV, and GND Pins are Connected Together)	R _{DS(ON)}	V _{DD2} = 13.2 V, I _O = 500 mA, T _J = 25 °C	--	170	--	mΩ
		V _{DD2} = 13.2 V, I _O = 500 mA, T _J = 150 °C	--	--	295	mΩ
		V _{DD2} = 9.0 V, I _O = 500 mA, T _J = 25 °C	--	170	--	mΩ
		V _{DD2} = 9.0 V, I _O = 500 mA, T _J = 150 °C	--	--	295	mΩ
		V _{DD2} = 5.0 V, I _O = 500 mA, T _J = 25 °C	--	176	--	mΩ
		V _{DD2} = 5.0 V, I _O = 500 mA, T _J = 150 °C	--	--	304	mΩ
		V _{DD2} = 3.0 V, I _O = 500 mA, T _J = 25 °C	--	255	--	mΩ
		V _{DD2} = 3.0 V, I _O = 500 mA, T _J = 150 °C	--	--	426	mΩ

Parameter	Symbol	Condition	Min	Typ	Max	Unit
LS FET on Resistance (SENSE_A, SENSE_B, GND_HV, and GND Pins are Connected Together, $R_{DS(ON)}$ with Sense Pin = GND, if Sense Pin V_{DD} = 0.5 V, Additional 100 mΩ at Worst Case)	$R_{DS(ON)}$	$V_{DD2} = 13.2 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25 \text{ }^{\circ}\text{C}$	--	182	--	mΩ
		$V_{DD2} = 13.2 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 150 \text{ }^{\circ}\text{C}$	--	--	332	mΩ
		$V_{DD2} = 9.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25 \text{ }^{\circ}\text{C}$	--	182	--	mΩ
		$V_{DD2} = 9.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 150 \text{ }^{\circ}\text{C}$	--	--	332	mΩ
		$V_{DD2} = 5.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25 \text{ }^{\circ}\text{C}$	--	185	--	mΩ
		$V_{DD2} = 5.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 150 \text{ }^{\circ}\text{C}$	--	--	338	mΩ
		$V_{DD2} = 3.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25 \text{ }^{\circ}\text{C}$	--	232	--	mΩ
		$V_{DD2} = 3.0 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 150 \text{ }^{\circ}\text{C}$	--	--	414	mΩ
Off-state Leakage Current	I_{OFF}	GPO0_HD, GPO1_HD ^[1] , $V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $85 \text{ }^{\circ}\text{C}$, PWM is off, including the charge pump OSC	23.2	--	32.9	μA
		GPO0_HD, GPO1_HD ^[1] , $V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $150 \text{ }^{\circ}\text{C}$, PWM is off, including the charge pump OSC	23.2	--	35.2	μA
		GPO2_HD, GPO3_HD, $V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $85 \text{ }^{\circ}\text{C}$, PWM is off, including the charge pump OSC	--	--	0.2	nA
		GPO2_HD, GPO3_HD, $V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $150 \text{ }^{\circ}\text{C}$, PWM is off, including the charge pump OSC	--	--	1.5	μA
Charge Pump Consumption Current (from V_{DD1} Pin or V_{DD2} Pin)	I_{CC}	$V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $150 \text{ }^{\circ}\text{C}$, PWM is off, including the charge pump OSC	--	--	200	μA
		$V_{DD2} = 5.0 \text{ V}$, $T_J = -40 \text{ }^{\circ}\text{C}$ to $150 \text{ }^{\circ}\text{C}$, PWM = 250 kHz	100	--	800	μA
Wake-up Time	t_{WAKE}	HV SLEEP OUT high to output transition, BG is always on, another pins SLEEP - disable	--	82.3	134	μs

[1] There is a resistive voltage divider in front of Diff Amplifier that is connected to GPO0_HD and GPO1_HD.

3.5 Protection Circuits

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Overcurrent Protection Threshold	I_{OCP}	Per any HS or LS FET	--	2.18	--	A
OCP Deglitch Time ^[1]	t_{OCP1}	$V_{DD} = 5 \text{ V}$, $V_{DD2} = 5 \text{ V}$, $T = 25 \text{ }^{\circ}\text{C}$, Deglitch = Enable, High Side	--	2.497	--	μs
		$V_{DD} = 5 \text{ V}$, $V_{DD2} = 5 \text{ V}$, $T = 25 \text{ }^{\circ}\text{C}$, Deglitch = Enable, Low Side	--	1.232	--	μs
OCP Retry Time ^[2]	t_{OCP2}	Delay = 492 μs	--	491	--	μs

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Recover from Undervoltage Lockout	V_{UVLO} [3]	At rising edge of V_{DD2}	--	--	2.90	V
Undervoltage Lockout		At falling edge of V_{DD2}	--	--	2.77	V
Thermal Shutdown Temperature	T_{TSD}	Junction temperature T_J	135	141	159	°C
Thermal Shutdown Hysteresis	T_{HYST}		--	16	--	°C
[1] OCP deglitch time option can be enabled by register [873] and register [875] separately for each Full Bridge. The High Side FETs do not have OCP deglitch time if the current through the FET is higher than I_{OCP} level during enable time. This is done to avoid huge currents during retry when the short is persist on the output. [2] OCP retry time can be selected separately for each HV OUT: HV GPO0 – registers [780:778], HV GPO1 – registers [788:786], HV GPO2 – registers [796:794], HV GPO3 – registers [804:802]. [3] UVLO function can be enabled separately for V_{DD2_A} by register [864] and V_{DD2_B} by register [865].						

4. Typical Application Circuit

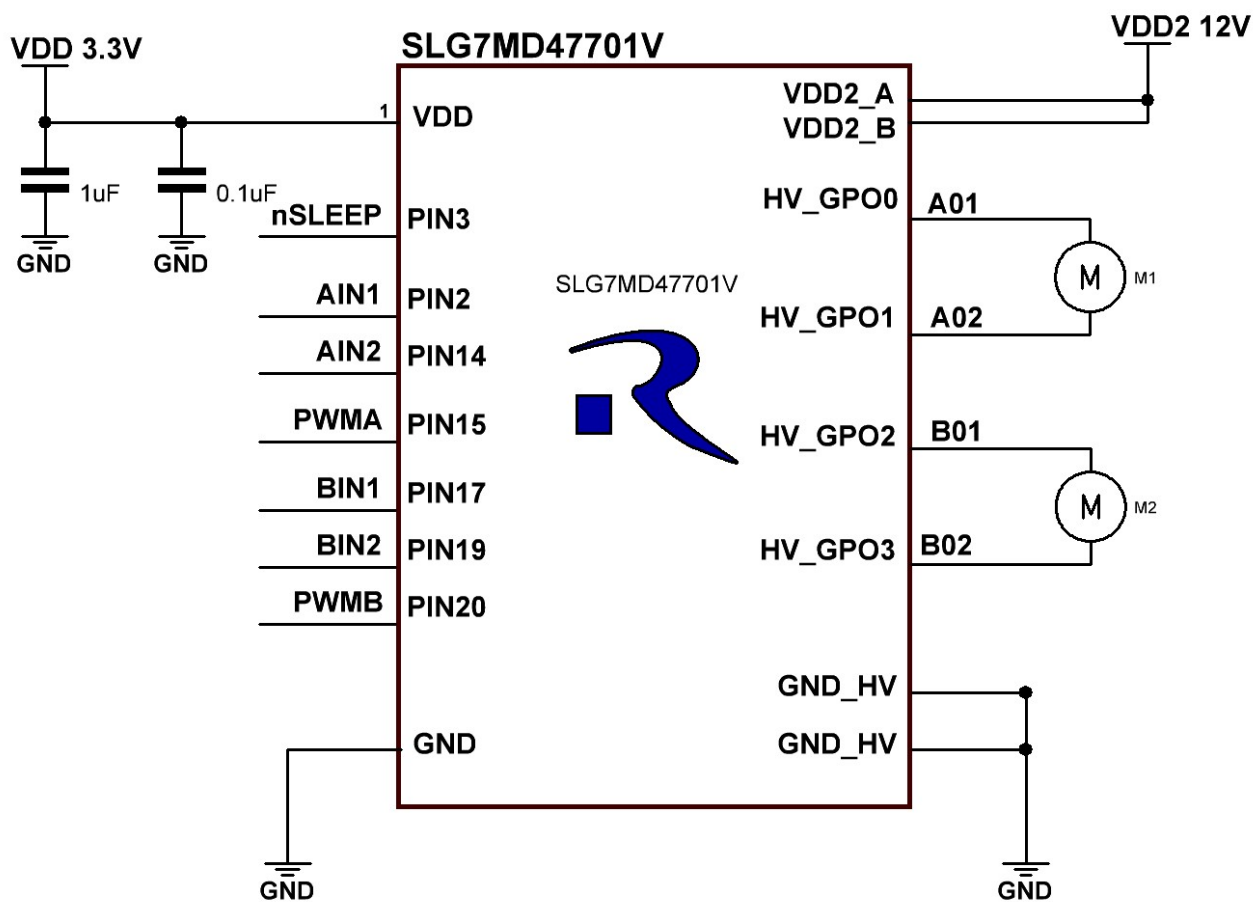


Figure 4. Typical Application Circuit

5. Functionality Waveforms

Channel 1 (yellow/top line) – PIN# 7 (A01) and PIN# 9 (B01), PIN# 2 (AIN1).

Channel 2 (light blue/2nd line) – PIN# 8 (A02) and PIN# 10 (B02), PIN# 4 (GND).

D0 – PIN# 3 (nSLEEP).

D1 – PIN# 2 (AIN1) or PIN# 17 (BIN1).

D2 – PIN# 14 (AIN2) or PIN# 19 (BIN2).

D3 – PIN# 15 (PWMA) or PIN# 20 (PWMB).

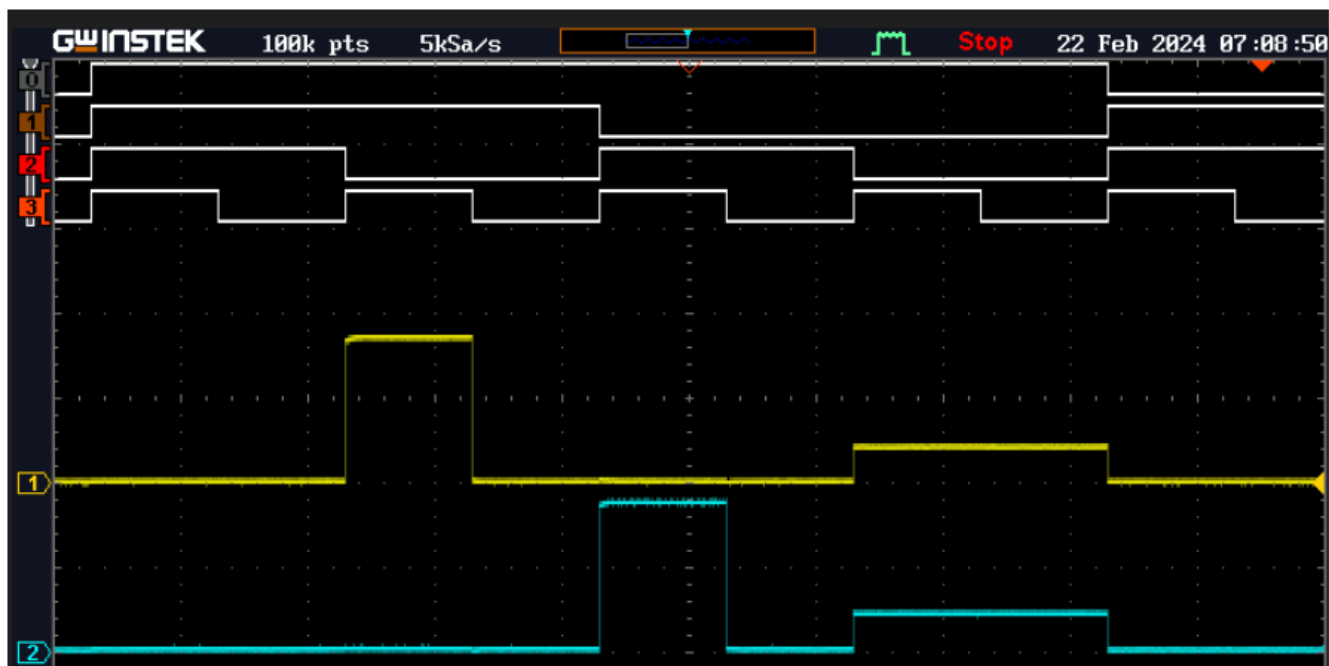
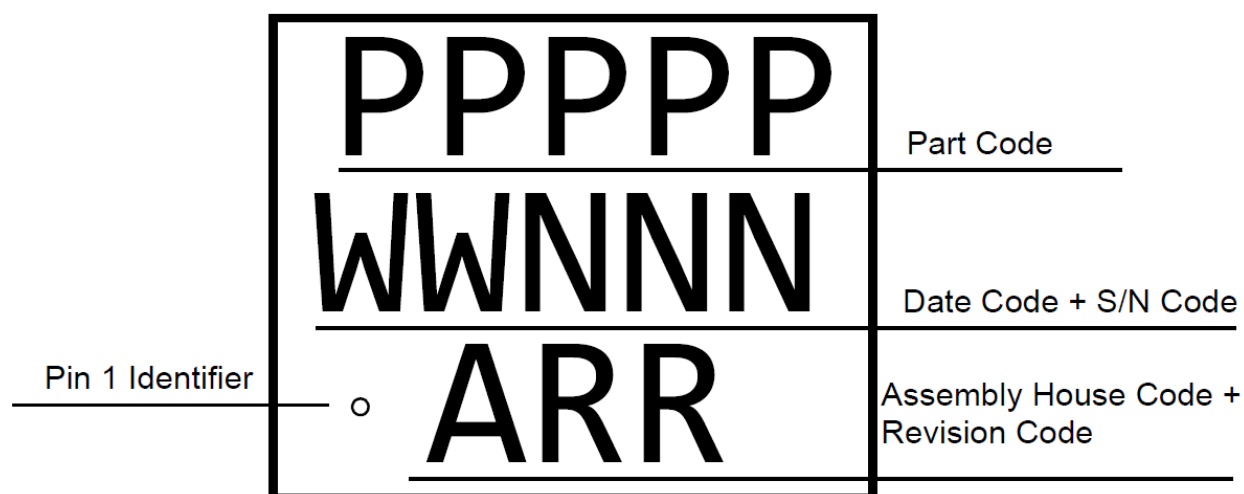


Figure 5. Chip Functionality

6. Package Top Marking Definitions



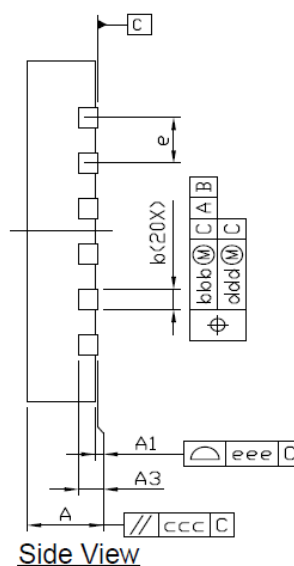
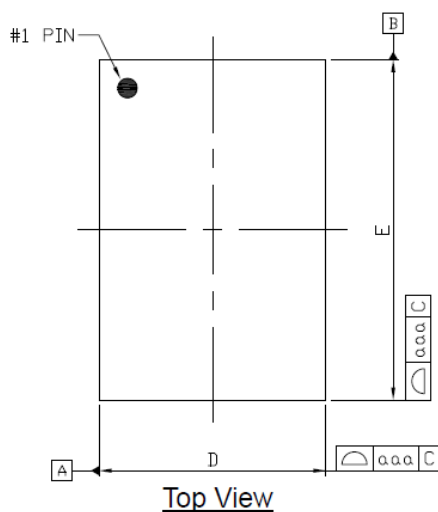
Datasheet Revision	Programming Code Number	Lock Status	Checksum	Part Code	Revision	Date
1.00	001	U	0xE9AB20C1			6/25/2024

Lock coverage for this part is indicated by $\sqrt{}$, from one of the following options:

$\sqrt{}$	Unlocked
	Partly lock read (mode 1)
	Partly lock read2 (mode 2)
	Partly lock read2/write (mode 3)
	All lock read (mode 4)
	All lock write (mode 5)
	All lock read/write (mode 6)

The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.

7. Package Outlines

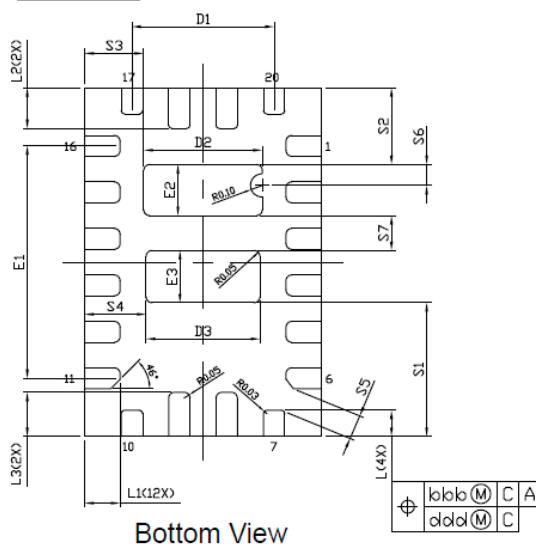


Notes:

1. All dimensions are in millimeters.
2. Dimension "b" applies to metalized terminal and is measured between 0.15 mm and 0.30 mm from the terminal tip. If the terminal has the optional radius on the other end of the terminal, the dimension "b" should not be measured in that radius area.
3. Bilateral coplanarity zone applies to the exposed heat sink slug as well as the terminal.

Controlling dimension: mm

Symbol	MILLIMETER			INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.000	0.020	0.050	0.000	0.001	0.002
A3	0.10	0.15	0.20	0.004	0.006	0.008
D	1.95	2.00	2.05	0.077	0.079	0.081
E	2.95	3.00	3.05	0.116	0.118	0.120
D1	1.15	1.20	1.25	0.045	0.047	0.049
E1	1.95	2.00	2.05	0.077	0.079	0.081
D2	0.95	1.00	1.05	0.037	0.039	0.041
E2	0.39	0.44	0.49	0.015	0.017	0.019
D3	0.91	0.96	1.01	0.036	0.038	0.040
E3	0.40	0.45	0.50	0.016	0.018	0.020
S1	1.10	1.15	1.20	0.043	0.045	0.047
S2	0.61	0.66	0.71	0.024	0.026	0.028
S3	0.45	0.50	0.55	0.018	0.020	0.022
S4	0.47	0.52	0.57	0.018	0.020	0.022
S5	0.208 REF			0.008 REF		
S6	0.180 REF			0.007 REF		
S7	0.300 REF			0.012 REF		

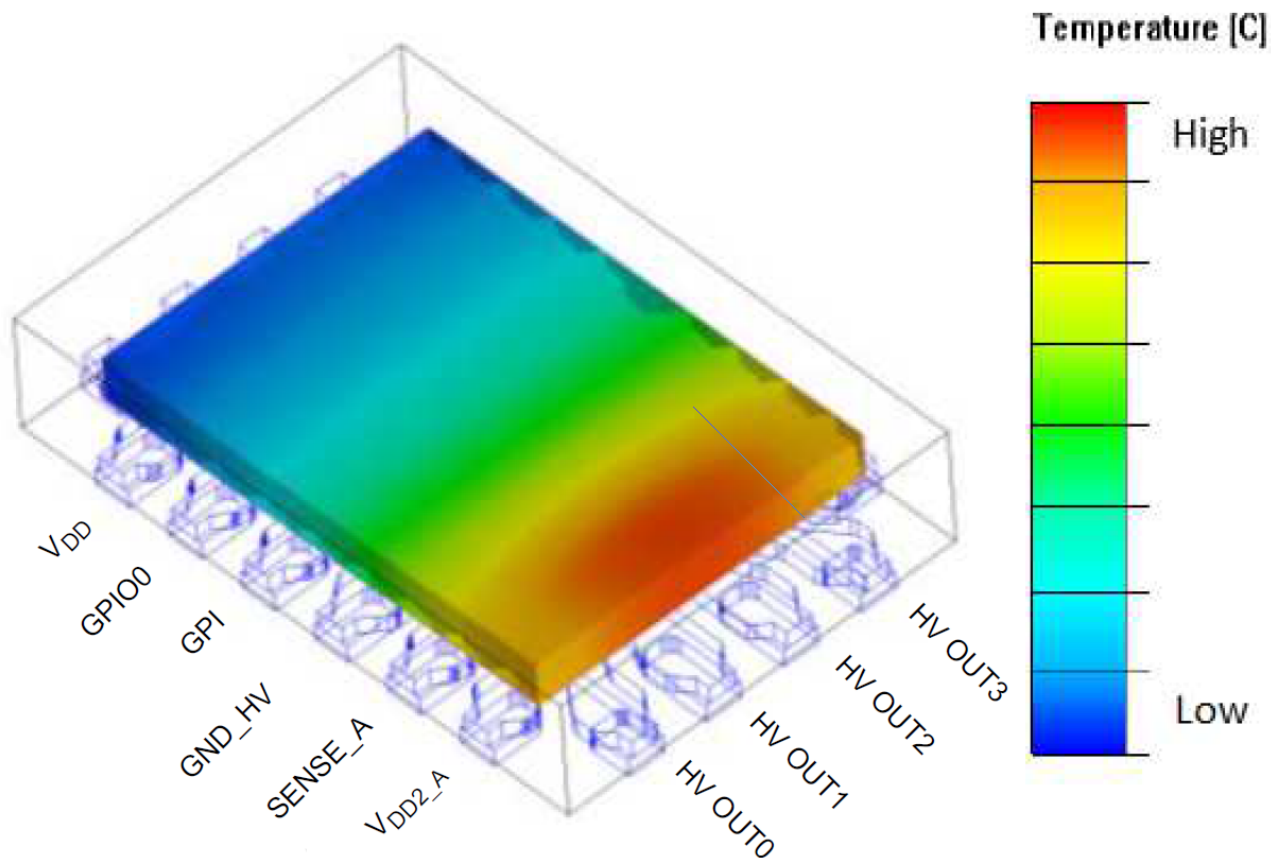


"A1" max lead coplanarity 0.05 mm
Standard tolerance: ± 0.05

Symbol	MILLIMETER			INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
e	0.40 BSC			0.016 BSC		
L	0.175	0.225	0.275	0.007	0.009	0.011
L1	0.250	0.300	0.350	0.010	0.012	0.014
L2	0.300	0.350	0.400	0.012	0.014	0.016
L3	0.330	0.380	0.430	0.013	0.015	0.017
b	0.130	0.180	0.230	0.005	0.007	0.009
aaa	0.07			0.003		
bbb	0.07			0.003		
ccc	0.1			0.004		
ddd	0.05			0.002		
eee	0.08			0.003		

8. Thermal Guidelines

Actual thermal characteristics will depend on number and position of vias, PCB type, copper layers, and other factors. Operating temperature range is from -40 °C to 85 °C. To guarantee reliable operation, the junction temperature of the SLG7MD47701 must not exceed 150 °C.



9. Layout Consideration

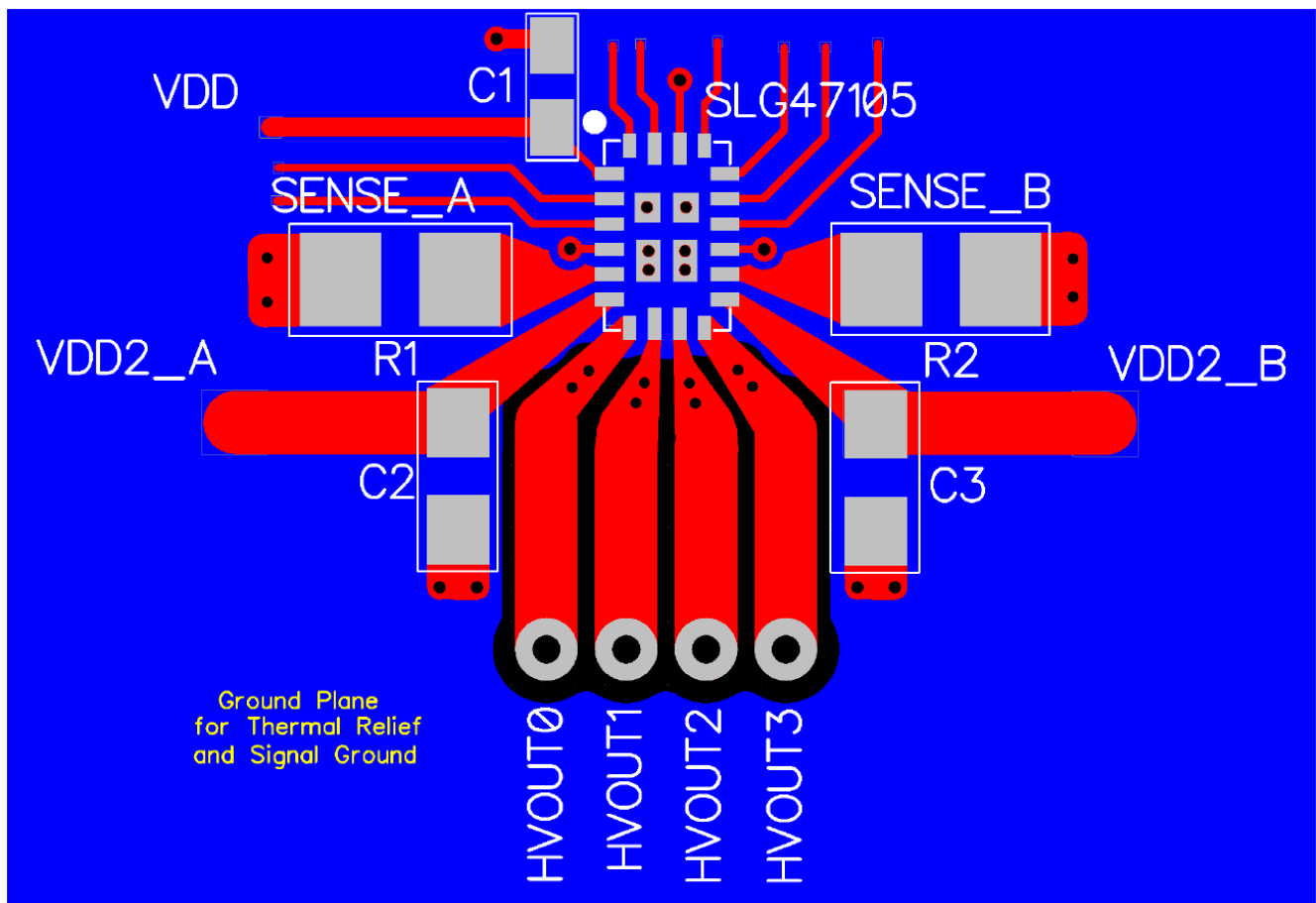
PCB should have enough ground plane to dissipate heat. SLG7MD47701 has two additional pads, which provide enhanced thermal dissipation. Thermal vias are used to transfer heat from chip to other layers of the PCB.

The sense resistors and power capacitors should be placed as close as possible to the chip for reducing parasitic parameters.

It is highly recommended to place low-ESR capacitor between V_{DD2_A} , V_{DD2_B} , and GND pin to keep input voltage stable and reduce ripple. This capacitor should be placed as close to the pins as possible. Also, the capacitor must have the low input impedance at the switching frequency. The recommended value of this capacitor is 1-10 μF for most applications. Motors with larger armature inductors require larger input capacitors.

Also, it is highly recommended to place 0.1 μF ceramic capacitor between V_{DD} and GND.

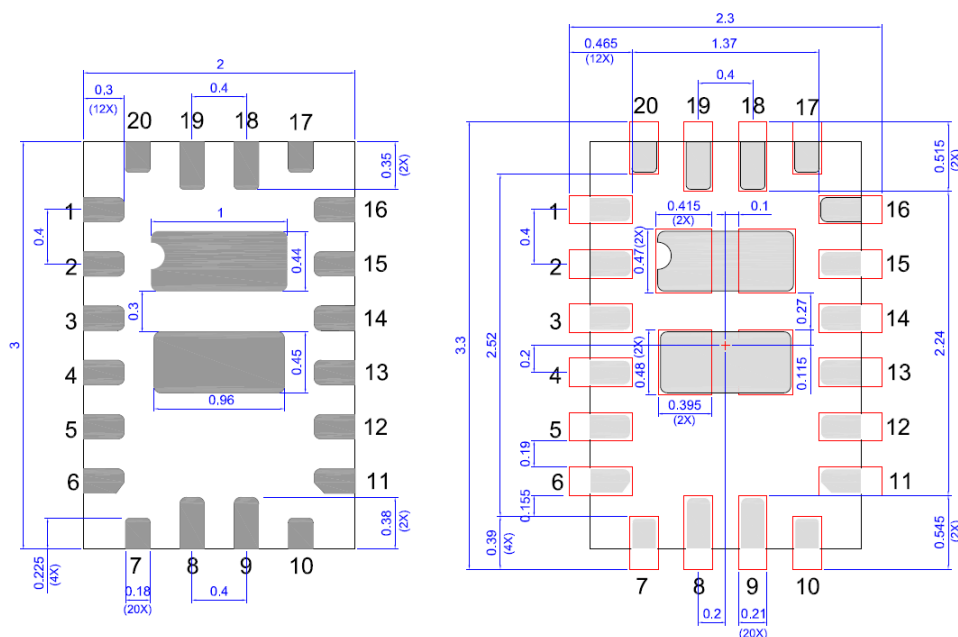
9.1 PCB Layout Example



10. Layout Guidelines

Expose Pad 
(Package face down)

Recommended Landing Pattern 
(Package face down)



10.1 Recommended Reflow Soldering Profile

Please see IPC/JEDEC J-STD-020. More information can be found at www.jedec.org.

11. Ordering Information

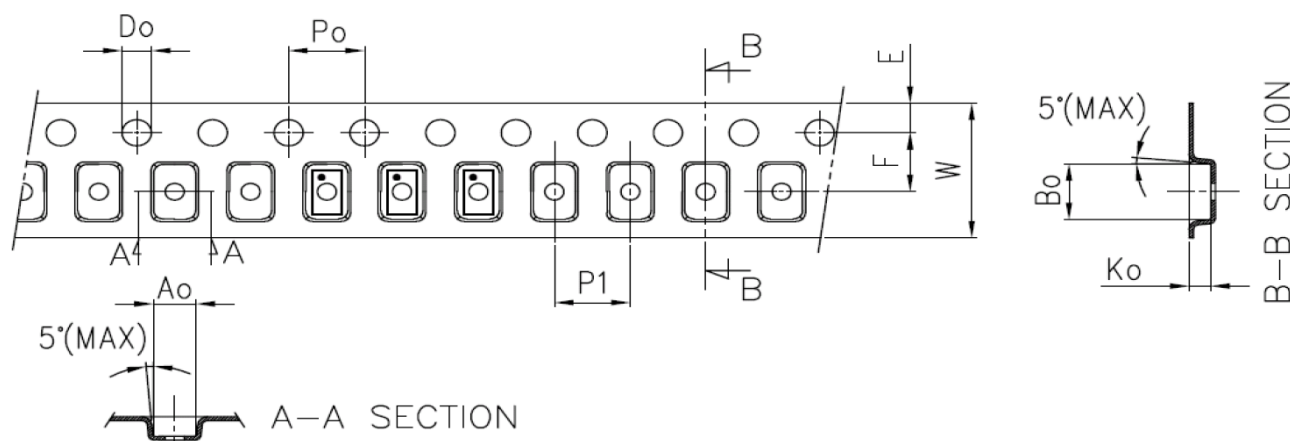
Part Number	Temperature Range
SLG7MD47701V	20-pin STQFN - Tape and Reel (3k units)

11.1 Tape and Reel Specification

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel & Hub Size [mm]	Leader (min)		Trailer (min)		Tape Width [mm]	Part Pitch [mm]
			per Reel	per Box		Pockets	Length [mm]	Pockets	Length [mm]		
STQFN 20L 2.0 mm x 3.0 mm 0.4P FCD Green	20	2.0x3.0x0.55	3000	3000	178/60	100	400	100	400	8	4

11.2 Carrier Tape Drawing and Dimensions

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	K0	P0	P1	D0	E	F	W
STQFN 20L 2.0 mm x 3.0 mm 0.4P FCD Green	2.2	3.15	0.76	4	4	1.5	1.75	3.5	8



12. Revision History

Revision	Date	Description
1.00	Jun 25, 2024	Initial release